



High-hfe, AF Amplifier Applications

Applications

· AF amplifier, various drivers, muting circuit.

Features

- · Ultrasmall-sized package permitting sets to be made smaller and slimer.
- · Adoption of FBET process.
- · High DC current gain : (h_{FE} =400 to 1000).
- · High breakdown voltage : (V_{CEO}≥100V).
- \cdot Low collector-to-emitter saturation voltage
 - $: (V_{CE(sat)} \le 0.5V).$
- · High V_{EBO} : $(V_{EBO} \ge 15V)$. · Small C_{ob} : $(C_{ob} = 4.0 pF typ)$.

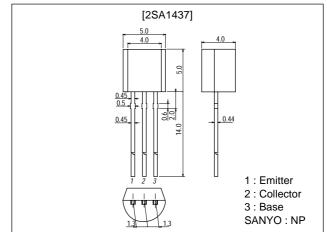
Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Package Dimensions

unit:mm

2003B

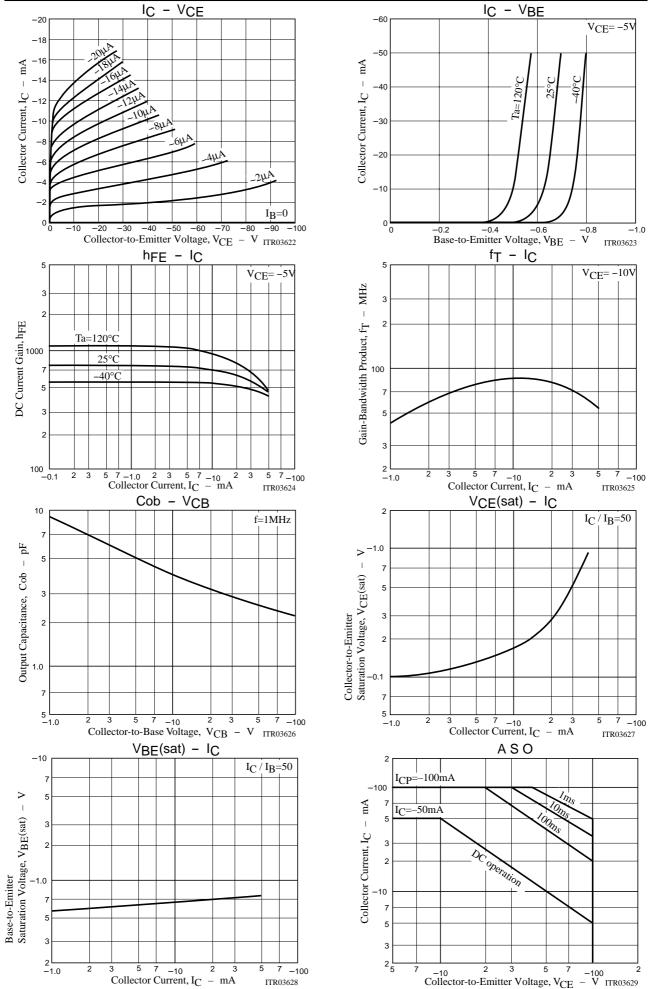


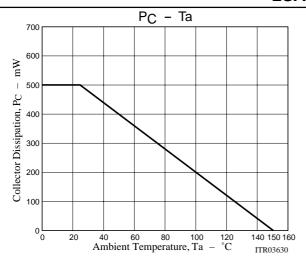
| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|------------------|------------|-------------|------|
| Collector-to-Base Voltage | VCBO | | -120 | V |
| Collector-to-Emitter Voltage | VCEO | | -100 | V |
| Emitter-to-Base Voltage | V _{EBO} | | -15 | V |
| Collector Current | lc | | -50 | mA |
| Collector Current (Pulse) | lCP | | -100 | mA |
| Collector Dissipation | PC | | 500 | mW |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---|----------------------|---|---------|-------|------|------|
| | | | min | typ | max | Onit |
| Collector Cutoff Current | I _{CBO} | V _{CB} =-80V, I _E =0 | | | -0.1 | μA |
| Emitter Cutoff Current | I _{EBO} | V _{EB} =-10V, I _C =0 | | | -0.1 | μA |
| DC Current Gain | hFE | V_{CE} =-5V, I_{C} =-10mA | 400 | 700 | 1000 | |
| Gain-Bandwidth Product | fŢ | V _{CE} =-10V, I _C =-10mA | | 85 | | MHz |
| Output Capacitance | C _{ob} | V _{CB} =-10V, f=1MHz | | 4.0 | | pF |
| Collector-to-Emitter Saturation Voltage | V _{CE(sat)} | I _C =-10mA, I _B =-0.2mA | | -0.18 | -0.5 | V |
| Base-to-Emitter Saturation Voltage | V _{BE(sat)} | I _C =-10mA, I _B =-0.2mA | | -0.7 | -1.0 | V |
| Collector-to-Base Breakdown Voltage | V(BR)CBO | I _C =-10μA, I _E =0 | -120 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | I _C =-1mA, R _{BE} =∞ | -100 | | | V |
| Emitter-to-Base Breakdown Votage | V _{(BR)EBO} | I _E =-10μA, I _C =0 | -15 | | | V |

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